

1、Features

- Low collector-emitter saturation voltage
- Complement to TIP127

2、Pinning information

PIN	Description	Simplified outline
1	Emitter(E)	
2	Collector(C)	
3	Base(B)	

3、Limiting value

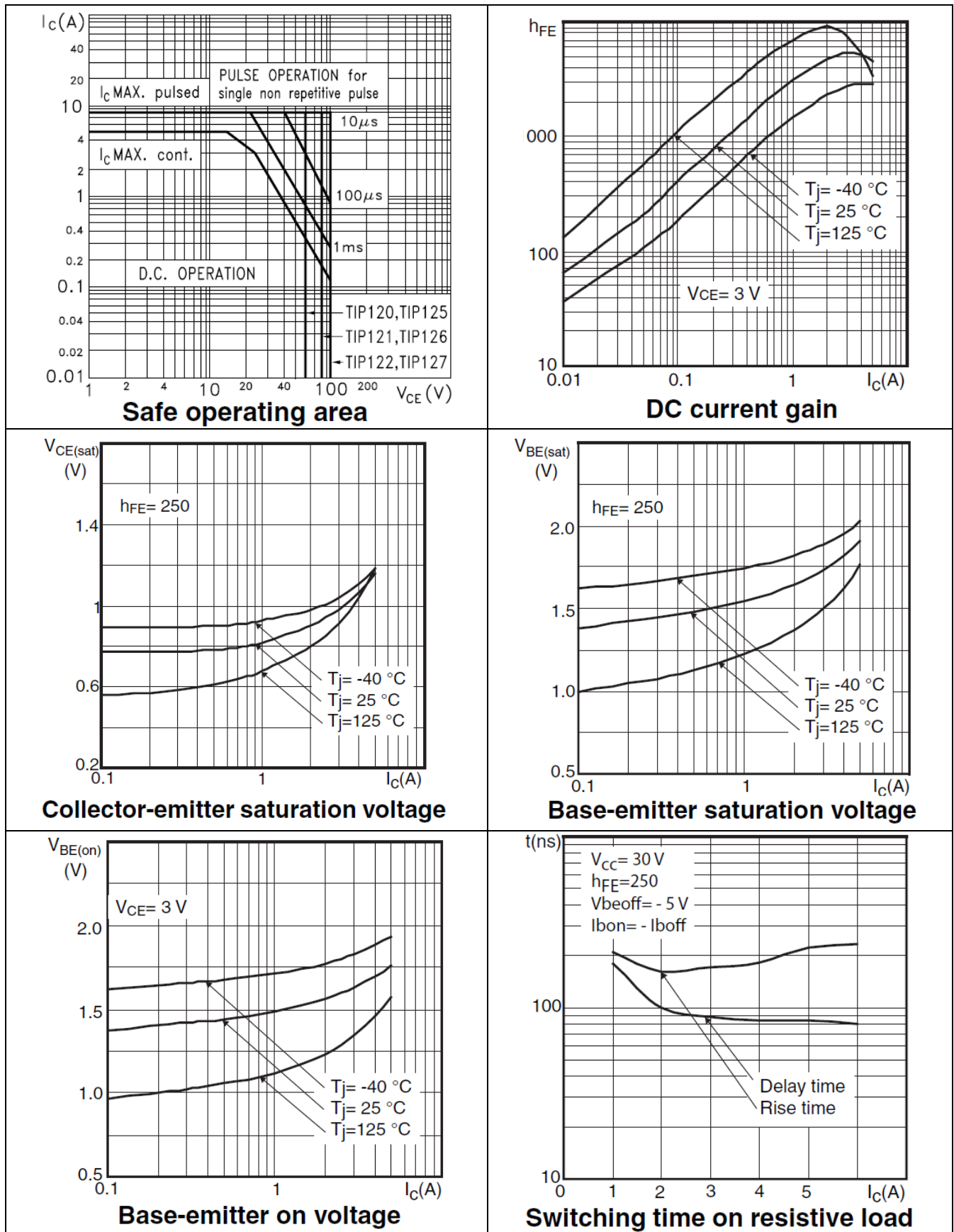
($T_a = 25^{\circ}\text{C}$ unless otherwise noted).

SYMBOL	PARAMETER	Limit	UNIT
Vcbo	Collector-Base Voltage	100	V
Vceo	Collector-Emitter Voltage	100	V
Vebo	Emitter-Base Voltage	5	V
Ic	Collector Current	DC	A
		Pulse	
Pd	Collector Power Dissipation		W
		TO-126	
Tj	Operating Junction Temperature	+125	$^{\circ}\text{C}$
Tstg	Operating Junction and Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$

4、Electrical Characteristics ($T_a = 25^{\circ}\text{C}$ unless otherwise noted)

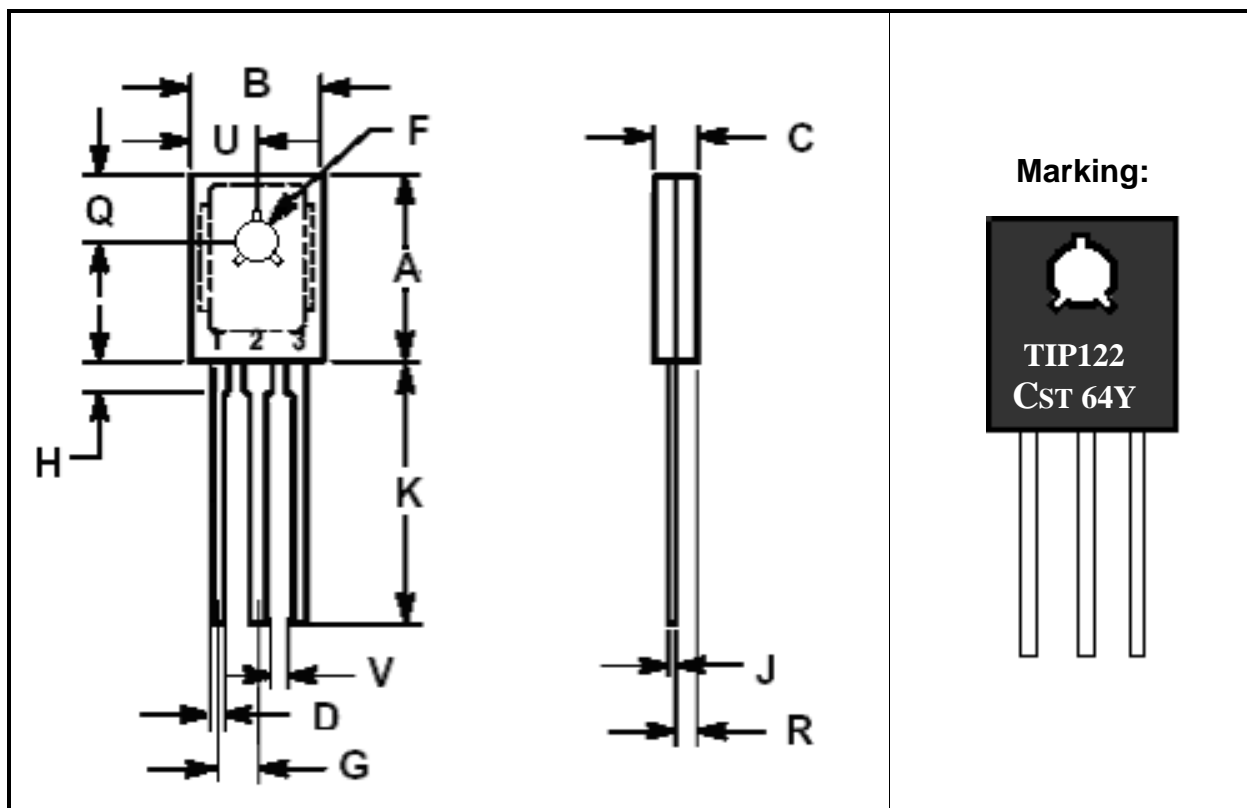
SYMBOL	PARAMETER	CONDITIONS	MIN	Typ	MAX	UNIT
BVcbo	Collector-Base Voltage	$I_C = 30\text{mA}, I_B = 0$	100			V
Bvceo	Collector-Emitter Breakdown Voltage	$I_C = 30\text{mA}, I_E = 0$	100			V
Bvebo	Emitter-Base Breakdown Voltage	$I_E = 10\text{mA}, I_C = 0$	5			V
Iceo	Collector Cutoff Current	$V_{CE} = 50\text{V}, I_E = 0$			0.5	mA
Iebo	Emitter Cutoff Current	$V_{EB} = 5\text{V}, I_C = 0$			2	mA
Vce(sat)	Collector-Emitter Saturation Voltage	$I_C / I_B = 3.0\text{A} / 12\text{mA}$			2.0	V
Vbe(on)	Base-Emitter On Voltage	$V_{CE} = 3\text{V}, I_C = 3\text{A}$			2.5	V
HFE	DC Current Gain	$V_{CE} = 3\text{V}, I_C = 3\text{A}$	1000			
		$V_{CE} = 3\text{V}, I_C = 0.5\text{A}$	1000			

5. Electrical Characteristics Curve



CST

6、Package outline(TO-126)



DIM	Inches			Millimeters		
	Min	Type	Max	Min	Type	Max
A	0.419	-	0.429	10.65	-	10.89
B	0.284	-	0.312	7.22	-	7.92
C	0.091	0.100	0.109	2.30	2.54	2.76
K	0.520	-	0.598	13.20	-	15.20
D	0.025	0.029	0.031	0.64	0.73	0.80
J	0.011	-	0.020	0.28	-	0.52
G	0.087	0.091	0.094	2.20	2.30	2.40
V	0.040	-	-	1.02	-	-
F	0.115	0.122	0.130	2.93	3.10	3.30
U	0.142	-	0.157	3.60	-	4.00
Q	0.151	-	0.163	3.83	-	4.13
H	0.071	0.102	0.114	1.80	2.6	2.90
R	0.045	-	0.065	1.15	-	1.65